

Thyristor Modules

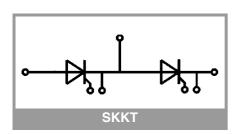
SKKT 58B16 E

Features*

- Heat transfer through aluminium oxide ceramic insulated metal baseplate
- UL recognized, file no. E63532

Typical Applications

- DC motor control (e. g. for machine tools)
- AC motor soft starters
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)



Symbol	Conditions	Values		Unit		
Chip						
I _{T(AV)}	sin. 180°	T _c = 85 °C		55		Α
.()	T _j = 130 °C	T _c = 100 °C	41		Α	
I _{TSM}		T _i = 25 °C		1500		Α
	– 10 ms	T _j = 130 °C		1200		Α
i ² t	_ 10 ms	T _i = 25 °C		11250		A ² s
		T _i = 130 °C		7200		A ² s
V _{RSM}	T _i = 25 °C		1700		V	
V _{RRM}	$T_{i} = 25 \text{ °C}$			1600		v
V _{DRM}	T _i = 25 °C			1600		v
(di/dt) _{cr}	$T_{i} = 130 \text{ °C}$		140		A/µs	
(dv/dt) _{cr}	$T_{i} = 130 ^{\circ}\text{C}$			1000		V/µs
T _j	,	-40 130			°C	
Module						
T _{stg}		-40 125		°C		
V _{isol}	a.c.; 50 Hz; r.m.s.	1 min	3000		V	
				3600		-
		1 s		3600		V
		1 S		3600		V
Characte	eristics	1 \$		3600		
Characte Symbol	eristics Conditions	15	min.		max.	
Symbol	1	15	min.	3600 typ.	max.	1
Symbol Chip	1	1	min.		max.	1
Symbol Chip V⊤	Conditions $T_j = 25 \text{ °C}, I_T = 180$	1	min.	typ.		Unit
Symbol Chip	Conditions	1	min.	typ. 1.5	1.75	Unit
Symbol Chip V _T V _{T(TO)} r _T	T _j = 25 °C, I _T = 180 T _j = 130 °C T _j = 130 °C	A	min.	typ. 1.5 0.85	1.75 1.00	Unit
Symbol Chip V _T V _T (TO) r _T I _{DD} ;I _{RD}	Conditions $T_j = 25 \ ^\circ C, I_T = 180$ $T_j = 130 \ ^\circ C$	A V _{DRM} ; V _{RD} = V _{RRM}	min.	typ. 1.5 0.85	1.75 1.00 4.8	Unit
Symbol Chip VT VT(TO) rT IDD;IRD tgql	Conditions $T_j = 25 \ ^\circ C$, $I_T = 180$ $T_j = 130 \ ^\circ C$ $T_j = 25 \ ^\circ C$, $V_{DD} =$ $T_j = 25 \ ^\circ C$, $I_G = 1 \ A$	A V _{DRM} ; V _{RD} = V _{RRM}	min.	typ. 1.5 0.85 4.00	1.75 1.00 4.8	Unit V V mΩ mA μs
Symbol Chip VT VT(TO) rT IDD;IRD tgd tgr	$\label{eq:conditions} \begin{split} \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ I_{T} &= 180 \\ \hline T_{j} &= 130 \ ^{\circ}\text{C} \\ \hline T_{j} &= 130 \ ^{\circ}\text{C} \\ \hline T_{j} &= 130 \ ^{\circ}\text{C}, \ V_{DD} &= \\ \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ I_{G} &= 1 \ \text{A} \\ \hline V_{D} &= 0.67 \ ^{*} \ V_{DRM} \end{split}$	A V _{DRM} ; V _{RD} = V _{RRM}	min.	typ. 1.5 0.85 4.00	1.75 1.00 4.8	Unit V V mΩ mA μs μs
Symbol Chip VT VT(TO) rT IDD;IRD tgq tgr tq	$\label{eq:transform} \begin{array}{c} \textbf{Conditions} \\ \hline T_{j} = 25 \ ^{\circ}\text{C}, \ \textbf{I}_{T} = 180 \\ \hline T_{j} = 130 \ ^{\circ}\text{C} \\ \hline T_{j} = 130 \ ^{\circ}\text{C}, \ \textbf{V}_{DD} = \\ \hline T_{j} = 25 \ ^{\circ}\text{C}, \ \textbf{I}_{G} = 1 \ \textbf{A} \\ \hline \textbf{V}_{D} = 0.67 \ ^{*} \ \textbf{V}_{DRM} \\ \hline T_{j} = 130 \ ^{\circ}\text{C} \end{array}$	A V _{DRM} ; V _{RD} = V _{RRM}	min.	typ. 1.5 0.85 4.00 1 2	1.75 1.00 4.8	Unit V V mΩ mA μs
Symbol Chip VT VT(TO) rT IDD;IRD tgd tgr Iq IH	$\label{eq:conditions} \begin{split} \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ I_{T} &= 180 \\ \hline T_{j} &= 130 \ ^{\circ}\text{C} \\ \hline T_{j} &= 130 \ ^{\circ}\text{C} \\ \hline T_{j} &= 130 \ ^{\circ}\text{C}, \ V_{DD} &= \\ \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ I_{G} &= 1 \ \text{A} \\ \hline V_{D} &= 0.67 \ ^{*} \ V_{DRM} \\ \hline T_{j} &= 130 \ ^{\circ}\text{C} \\ \hline T_{j} &= 25 \ ^{\circ}\text{C} \end{split}$	A V _{DRM} ; V _{RD} = V _{RRM} , di _G /dt = 1 A/μs	min.	typ. 1.5 0.85 4.00 1 2 170	1.75 1.00 4.8 20	Unit V V mΩ mA μs μs μs
Symbol Chip VT VT(TO) rT IDD;IRD tgd tgr tq IH IL	$\label{eq:conditions} \begin{split} \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ I_{T} &= 180 \\ \hline T_{j} &= 130 \ ^{\circ}\text{C} \\ \hline T_{j} &= 130 \ ^{\circ}\text{C} \\ \hline T_{j} &= 130 \ ^{\circ}\text{C}, \ V_{DD} &= \\ \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ I_{G} &= 1 \ \text{A} \\ \hline V_{D} &= 0.67 \ ^{*} \ V_{DRM} \\ \hline T_{j} &= 130 \ ^{\circ}\text{C} \\ \hline T_{j} &= 25 \ ^{\circ}\text{C} \\ \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ R_{G} &= 33 \end{split}$	A V _{DRM} ; V _{RD} = V _{RRM} , di _G /dt = 1 A/μs		typ. 1.5 0.85 4.00 1 2 170 150	1.75 1.00 4.8 20 250	Unit V V mΩ mA μs μs μs mA
Symbol Chip VT VT(TO) rT IDD;IRD tgd tgr tq IH L VGT	$\label{eq:conditions} \begin{split} \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ I_{T} &= 180 \\ \hline T_{j} &= 130 \ ^{\circ}\text{C} \\ \hline T_{j} &= 130 \ ^{\circ}\text{C} \\ \hline T_{j} &= 130 \ ^{\circ}\text{C}, \ V_{DD} &= \\ \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ I_{G} &= 1 \ \text{A} \\ \hline V_{D} &= 0.67 \ ^{*} \ V_{DRM} \\ \hline T_{j} &= 130 \ ^{\circ}\text{C} \\ \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ T_{g} &= 33 \\ \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ R_{G} &= 33 \\ \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ d.c. \end{split}$	A V _{DRM} ; V _{RD} = V _{RRM} , di _G /dt = 1 A/μs	2.5	typ. 1.5 0.85 4.00 1 2 170 150	1.75 1.00 4.8 20 250	Unit V V MΩ MA μs μs mA mA V
Symbol Chip VT VT(TO) rT IDD;IRD tgd tgr tq IH IL VGT IGT	$\label{eq:conditions} \begin{split} \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ \text{I}_{T} &= 180 \\ \hline T_{j} &= 130 \ ^{\circ}\text{C} \\ \hline T_{j} &= 130 \ ^{\circ}\text{C} \\ \hline T_{j} &= 130 \ ^{\circ}\text{C}, \ V_{DD} &= \\ \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ \text{I}_{G} &= 1 \ \text{A} \\ \hline V_{D} &= 0.67 \ ^{*} \ V_{DRM} \\ \hline T_{j} &= 130 \ ^{\circ}\text{C} \\ \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ \ T_{g} &= 25 \ ^{\circ}\text{C}, \ \ T_{g} &= 33 \\ \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ \ \text{d.c.} \\ \hline T_{j} &= 25 \ ^{\circ}\text{C}, \ \ \text{d.c.} \end{split}$	A V _{DRM} ; V _{RD} = V _{RRM} , di _G /dt = 1 A/μs		typ. 1.5 0.85 4.00 1 2 170 150	1.75 1.00 4.8 20 250 600	Unit V V mΩ mA μs μs μs mA mA
Symbol Chip VT VT(TO) rT IDD;IRD tgd tgr tq IH IC VGT IGT VGD	$\label{eq:result} \begin{array}{ c c c c } \hline Conditions \\ \hline T_{j} = 25 \ ^{\circ}C, \ I_{T} = 180 \\ \hline T_{j} = 130 \ ^{\circ}C \\ \hline T_{j} = 130 \ ^{\circ}C \\ \hline T_{j} = 130 \ ^{\circ}C, \ V_{DD} = \\ \hline T_{j} = 25 \ ^{\circ}C, \ I_{G} = 1 \ A \\ \hline V_{D} = 0.67 \ ^{*}V_{DRM} \\ \hline T_{j} = 130 \ ^{\circ}C \\ \hline T_{j} = 25 \ ^{\circ}C, \ R_{G} = 33 \\ \hline T_{j} = 25 \ ^{\circ}C, \ d.c. \\ \hline T_{j} = 25 \ ^{\circ}C, \ d.c. \\ \hline T_{j} = 130 \ ^{\circ}C, \ d.c. \\ \hline \end{array}$	A V _{DRM} ; V _{RD} = V _{RRM} , di _G /dt = 1 A/μs	2.5	typ. 1.5 0.85 4.00 1 2 170 150	1.75 1.00 4.8 20 250	Unit V V mΩ mA μs μs mA mA V V mA
Symbol Chip VT VT(TO) rT IDD;IRD tgd tgd tgr tgl UH IL VGT IGT	Conditions $T_j = 25 \ ^\circ C, I_T = 180$ $T_j = 130 \ ^\circ C$ $T_j = 130 \ ^\circ C$ $T_j = 130 \ ^\circ C$ $T_j = 130 \ ^\circ C, V_{DD} =$ $T_j = 25 \ ^\circ C, I_G = 1 \ A$ $V_D = 0.67 \ ^* V_{DRM}$ $T_j = 25 \ ^\circ C, R_G = 33$ $T_j = 25 \ ^\circ C, R_G = 33$ $T_j = 25 \ ^\circ C, d.c.$ $T_j = 130 \ ^\circ C, d.c.$ $T_j = 130 \ ^\circ C, d.c.$ $T_j = 130 \ ^\circ C, d.c.$	A $V_{DRM}; V_{RD} = V_{RRM}$ $d_{ig}/dt = 1 A/\mu s$ Ω	2.5	typ. 1.5 0.85 4.00 1 2 170 150	1.75 1.00 4.8 20 250 600 0.25 4	Unit V mΩ mA μs mA v mA
Symbol Chip VT VT(TO) rT IDD;IRD tgd tgr tq IH IC VGT IGT VGD	$\label{eq:result} \begin{array}{ c c c c } \hline Conditions \\ \hline T_{j} = 25 \ ^{\circ}C, \ I_{T} = 180 \\ \hline T_{j} = 130 \ ^{\circ}C \\ \hline T_{j} = 130 \ ^{\circ}C \\ \hline T_{j} = 130 \ ^{\circ}C, \ V_{DD} = \\ \hline T_{j} = 25 \ ^{\circ}C, \ I_{G} = 1 \ A \\ \hline V_{D} = 0.67 \ ^{*}V_{DRM} \\ \hline T_{j} = 130 \ ^{\circ}C \\ \hline T_{j} = 25 \ ^{\circ}C, \ R_{G} = 33 \\ \hline T_{j} = 25 \ ^{\circ}C, \ d.c. \\ \hline T_{j} = 25 \ ^{\circ}C, \ d.c. \\ \hline T_{j} = 130 \ ^{\circ}C, \ d.c. \\ \hline \end{array}$	A V_{DRM} ; $V_{RD} = V_{RRM}$, di _G /dt = 1 A/μs Ω per chip	2.5	typ. 1.5 0.85 4.00 1 2 170 150	1.75 1.00 4.8 20 250 600 0.25 4 0.42	Unit V V MΩ mA μs μs mA MA V MA V MA K/W
Symbol Chip V _T V _{T(TO)} r _T l _{DD} ;l _{RD} t _{gd} t _{gd} t _{gr} t _q l _H l _L V _{GT} l _{GD}	Conditions $T_j = 25 \ ^\circ C, I_T = 180$ $T_j = 130 \ ^\circ C$ $T_j = 130 \ ^\circ C$ $T_j = 130 \ ^\circ C$ $T_j = 130 \ ^\circ C, V_{DD} =$ $T_j = 25 \ ^\circ C, I_G = 1 \ A$ $V_D = 0.67 \ ^* V_{DRM}$ $T_j = 25 \ ^\circ C, R_G = 33$ $T_j = 25 \ ^\circ C, R_G = 33$ $T_j = 25 \ ^\circ C, d.c.$ $T_j = 130 \ ^\circ C, d.c.$ $T_j = 130 \ ^\circ C, d.c.$ $T_j = 130 \ ^\circ C, d.c.$	A $V_{DRM}; V_{RD} = V_{RRM}$ $d_{ig}/dt = 1 A/\mu s$ Ω	2.5	typ. 1.5 0.85 4.00 1 2 170 150	1.75 1.00 4.8 20 250 600 0.25 4	V V mΩ mA μs μs mA V mA V mA V mA V mA V

R_{th(j-c)} rec. 120° Module Rth(c,c)

R _{th(c-s)}	chip	0.0	0.09	
	module	0.0	0.05	
Ms	to heatsink M5	4.25	5.75	Nm
Mt	to terminals M5	2.55	3.45	Nm
а			5 * 9.81	m/s²
w		75	75	

per module

per module

per chip

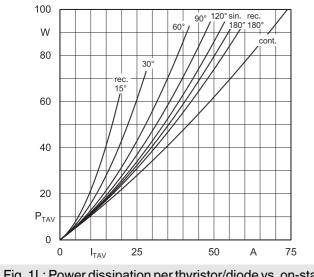
© by SEMIKRON

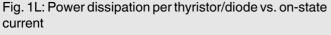
0.51

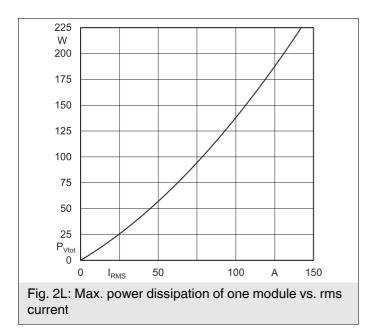
0.255

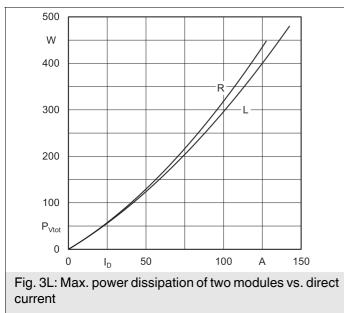
K/W K/W

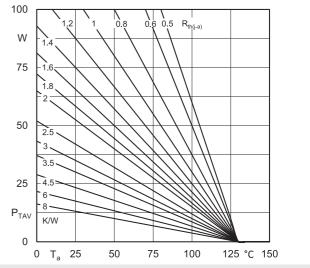
K/W













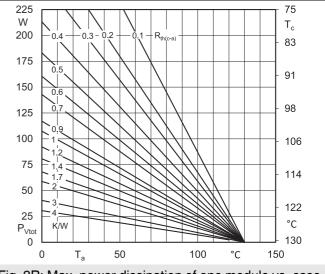


Fig. 2R: Max. power dissipation of one module vs. case temperature

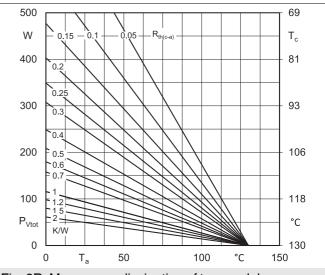
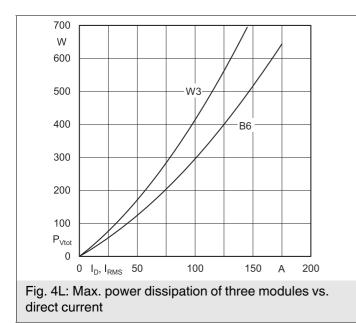
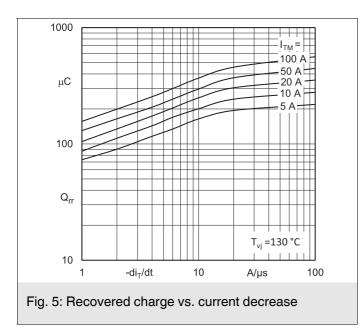
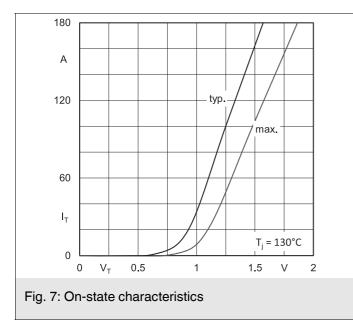


Fig. 3R: Max. power dissipation of two modules vs. case temperature







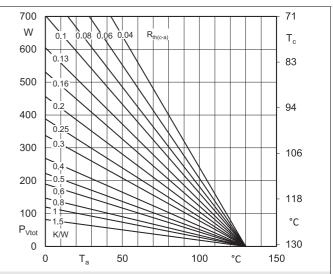


Fig. 4R: Max. power dissipation of three modules vs. case temperature

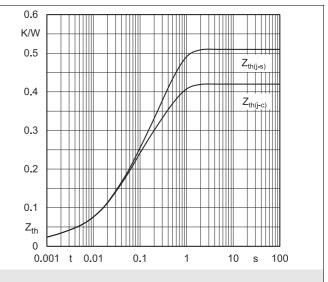
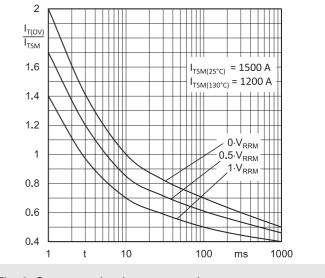
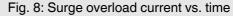
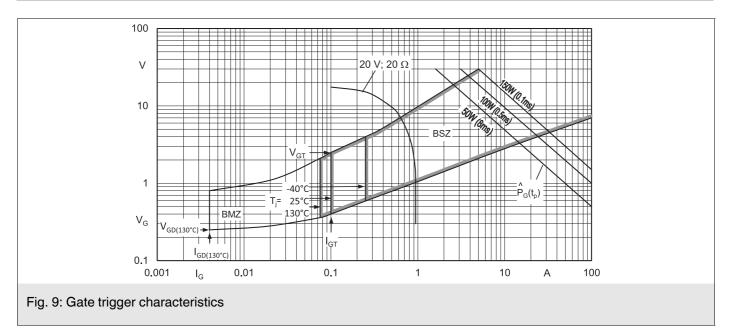
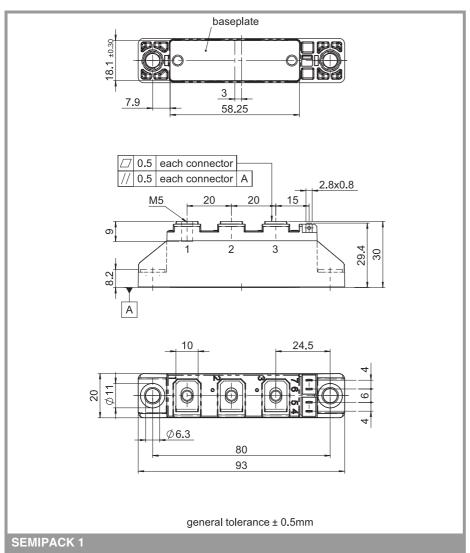


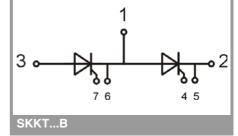
Fig. 6: Transient thermal impedance vs. time











This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

*IMPORTANT INFORMATION AND WARNINGS

The specifications of SEMIKRON products may not be considered as guarantee or assurance of product characteristics ("Beschaffenheitsgarantie"). The specifications of SEMIKRON products describe only the usual characteristics of products to be expected in

typical applications, which may still vary depending on the specific application. Therefore, products must be tested for the respective application in advance. Application adjustments may be necessary. The user of SEMIKRON products is responsible for the safety of their applications embedding SEMIKRON products and must take adequate safety measures to prevent the applications from causing a physical injury, fire or other problem if any of SEMIKRON products become faulty. The user is responsible to make sure that the application design is compliant with all applicable laws, regulations, norms and standards. Except as otherwise explicitly approved by SEMIKRON in a written document signed by authorized representatives of SEMIKRON, SEMIKRON products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury. No representation or warranty is given and no liability is assumed with respect to the accuracy, completeness and/or use of any information herein, including without limitation, warranties of non-infringement of intellectual property rights of any third party. SEMIKRON does not assume any liability arising out of the applications or use of any product; neither does it convey any license under its patent rights, copyrights, trade secrets or other intellectual property rights of any third party which may arise from applications. Due to technical requirements our products may contain dangerous substances. For information on the types in question please contact the nearest SEMIKRON sales office. This document supersedes and replaces all information previously supplied and may be superseded by updates. SEMIKRON reserves the right to make changes.